





150V NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

Features

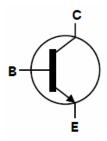
- BV_{CEO} > 150V
- Maximum Continuous Current I_{C(cont)} = 4A
- Up to 10A Peak Current
- Low Saturation Voltage
- P_D = 1.2W
- Lead-Free Finish; RoHS compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

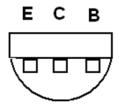
- Case: E-Line (TO-92 Compatible)
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.159 grams (approximate)







Device Symbol



Bottom View Pin-Out

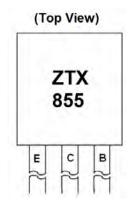
Ordering Information (Note 4)

Product	Marking	Package	Quantity per box on tape
ZTX855STZ	ZTX855	E-Line	2,000
ZTX855	ZTX855	E-Line	4,000 loose

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



ZTX855 = Product type Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

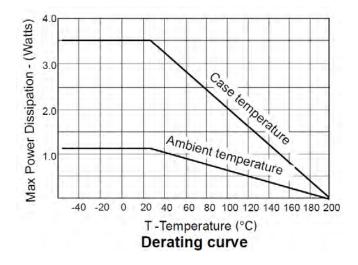
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	250	V
Collector-Emitter Voltage	V_{CEO}	150	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	lc	4	Α
Peak Pulse Current	I _{CM}	10	А

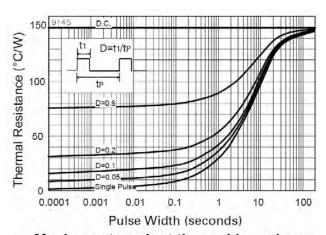
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Practical Power Dissipation (Note 5)	P _{DP}	1.58	W
Power Dissipation	P _D	1.2	W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	150	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	50	°C/W
Operating and Storage Temperature Range	T_{J}, T_{STG}	-55 to +200	°C

Notes: 5. For devices mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum.

Thermal Characteristics









ZTX855

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

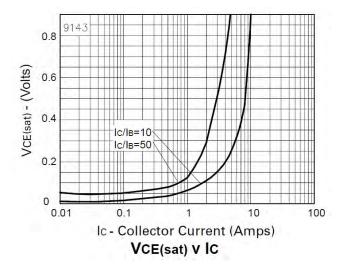
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	250	375	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	250	375	_	V	$I_C = 1\mu A,RB \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 6)	BV _{CEO}	150	180	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	6	8	_	V	$I_{E} = 100 \mu A$
Collector Cut-off Current	I _{CBO}	-	-	50 1	nΑ μΑ	V _{CB} = 200V V _{CB} = 200V, @T _A = 100°C
Collector Cut-off Current	l _{CER} R≤1kΩ	-	-	50 1	nΑ μΑ	V _{CB} = 200V V _{CB} = 200V, @T _A = 100°C
Emitter Cut-off Current	I _{EBO}	-	-	10	nA	$V_{EB} = 6V$
Collector-Emitter Saturation Voltage (Note 6)	V _{CE(sat)}	=	20 35 60 210	40 60 100 260	mV	$I_C = 100$ mA, $I_B = 5$ mA $I_C = 500$ mA, $I_B = 50$ mA $I_C = 1$ A, $I_B = 100$ mA $I_C = 4$ A, $I_B = 400$ mA
Base-Emitter Saturation Voltage (Note 6)	$V_{BE(sat)}$	-	960	1100	mV	$I_C = 4A$, $I_B = 400mA$
Base-Emitter Turn-On Voltage (Note 6)	$V_{BE(on)}$	-	0.88	1.0	V	$I_C = 4A$, $V_{CE} = 5V$
DC Current Gain (Note 6)	hFE	100 100 35	200 200 55 10	- 300 - -		$I_C = 10 \text{mA}, V_{CE} = 5 \text{V}$ $I_C = 1 \text{A}, V_{CE} = 5 \text{V}$ $I_C = 4 \text{A}, V_{CE} = 5 \text{V}$ $I_C = 10 \text{A}, V_{CE} = 5 \text{V}$
Current Gain-Bandwidth Product (Note 6)	f _T	-	90	-	MHz	$V_{CE} = 10V, I_{C} = 100mA$ f = 50MHz
Output Capacitance (Note 6)	C _{obo}		22		pF	V _{CB} = 20V. f = 1MHz
Switching Times	t _{on} t _{off}	_	66 2130	_	ns ns	$I_C = 1A$, $I_{B1} = 100mA$ $I_{B2} = 100mA$, $V_{CC} = 50V$

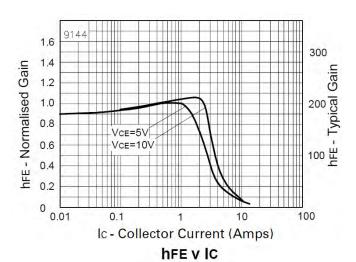
Notes: 6. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%

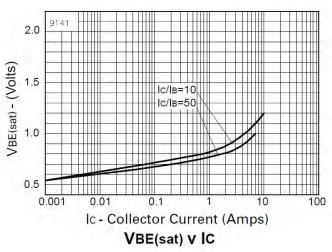


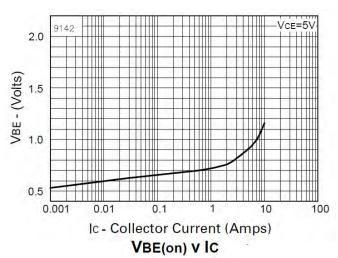
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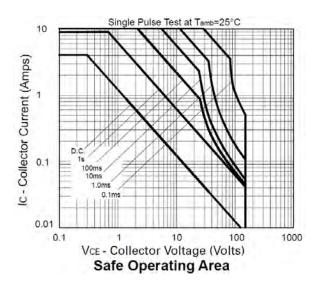
Typical Characteristics









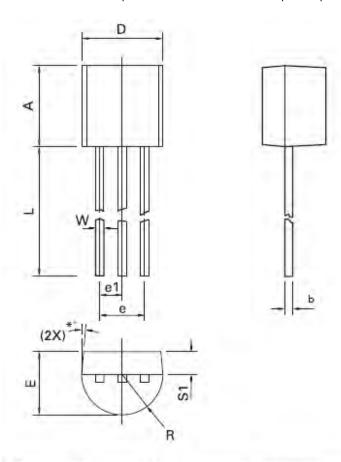






Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



Dim.	Millin	neters	Inc	ies
	Min.	Max.	Min.	Max.
Α	4.32	4.95	0.170	0.195
b	0.36	0.51	0.014	0.020
E	3.30	3.94	0.130	0.155
е	2.41	2.67	0.095	0.105
e1	1.14	1.40	0.045	0.055
L	12.70	15.49	0.500	0.610
R	2.16	2.41	0.085	0.095
S1	1.14	1,52	0.045	0.060
W	0.41	0.56	0.016	0.022
D	4.45	4.95	0.175	0.195
*0	4°	6°	4°	6°

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches





ZTX855

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